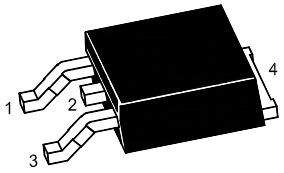
ST 2SB1261R

PNP Silicon Epitaxial Planar Transistor

for power switching and amplifier applications



1. Base 2. Collector 3. Emitter 4. Collector
TO-252 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	60	V
Collector Emitter Voltage	$-V_{CEO}$	60	V
Emitter Base Voltage	$-V_{EBO}$	7	V
Collector Current	$-I_C$	3	A
Collector Current (10 ms)	$-I_{CP}$	5	A
Base Current	$-I_B$	0.5	A
Power Dissipation (T_a = 25 °C)	P_{tot}	2	W
Power Dissipation (T_c = 25 °C)	P_{tot}	10	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}$ = 2 V, $-I_C$ = 0.6 A	Current Gain Group M	h_{FE}	100	-	200	-
	L	h_{FE}	160	-	320	-
	K	h_{FE}	200	-	400	-
at $-V_{CE}$ = 2 V, $-I_C$ = 2 A		h_{FE}	50	-	-	-
Collector Base Cutoff Current at $-V_{CB}$ = 60 V		$-I_{CBO}$	-	-	10	µA
Emitter Base Cutoff Current at $-V_{EB}$ = 7 V		$-I_{EBO}$	-	-	10	µA
Collector Emitter Saturation Voltage at $-I_C$ = 1.5 A, $-I_B$ = 0.15 A		$-V_{CE(sat)}$	-	-	0.3	V
Base Emitter Saturation Voltage at $-I_C$ = 1.5 A, $-I_B$ = 0.15 A		$-V_{BE(sat)}$	-	-	1.2	V
Transition Frequency at $-V_{CE}$ = 5 V, $-I_C$ = 1.5 A		f_T	-	50	-	MHz
Turn On Time at $-I_C$ = 1 A, $-I_B = I_B$ = 100 mA, $-V_{CC}$ = 10 V, R_L = 10 Ω		t_{on}	-	-	0.5	µs
Storage Time at $-I_C$ = 1 A, $-I_B = I_B$ = 100 mA, $-V_{CC}$ = 10 V, R_L = 10 Ω		t_{stg}	-	-	2	µs
Fall Time at $-I_C$ = 1 A, $-I_B = I_B$ = 100 mA, $-V_{CC}$ = 10 V, R_L = 10 Ω		t_f	-	-	0.5	µs

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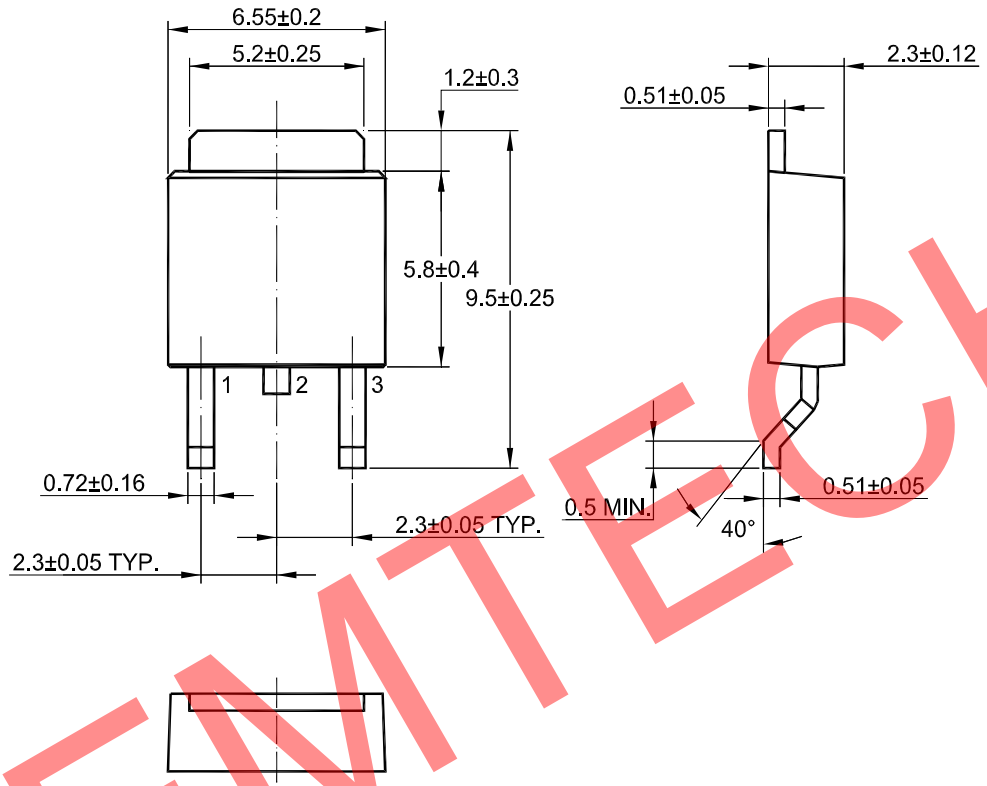
ISO/TS 16949 : 2009 Certificate No. 05103 | ISO14001 : 2004 Certificate No. 7116 | ISO 9001 : 2008 Certificate No. 0506098 | BS-OHSAS 18001 : 2007 Certificate No. 7116 | IECQ QC 080000

Dated : 23/09/2009

TO-252 PACKAGE OUTLINE



Dimensions in mm